

	Type	L #	Hits	Search Text	DBs	Comments
1	BRS	L1	346353	438/\$.ccls. 257/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
2	BRS	L2	108108	1 and (transistor or MOS or CMOS)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
3	BRS	L3	20	2 and (densify\$3 or densification) near (spacer or sidewall)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
4	BRS	L4	15	3 and nitrogen	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
5	BRS	L5	14	4 and (silicide or salicide or polycide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
6	BRS	L6	6	(lowe-brett-d or smythe-john-a or carns-tomothy-k).in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
7	BRS	L7	4	((densify\$3 or densification) near (spacer or sidewall)).ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
8	BRS	L8	36	((densify\$3 or densification) near (spacer or sidewall))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
9	BRS	L9	22	8 and (silicide or salicide or polycide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
10	BRS	L10	21	9 and (transistor or MOS or CMOS)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
11	BRS	L11	2639	spacer near oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
12	BRS	L12	100	11 and (densify\$3 or densification)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
13	BRS	L13	72	12 and (silicide or salicide or polycide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
14	BRS	L14	8	densifi\$5 near spacer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	